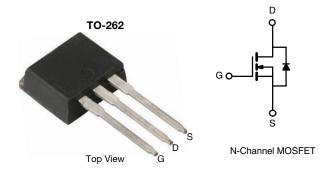


Automotive N-Channel 60 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	60				
$R_{DS(on)} (\Omega)$ at $V_{GS} = 10 V$	0.00470				
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = 4.5 V	0.00600				
I _D (A)	120				
Configuration	Single				
Package	TO-262				



FEATURES

- TrenchFET[®] power MOSFET
- · Package with low thermal resistance
- AEC-Q101 qualified d
- 100 % $\rm R_g$ and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	60	V	
Gate-Source Voltage		V _{GS}	± 20		
Continuous Drain Current	$T_C = 25 \ ^\circ C \ ^a$	I-	120		
	T _C = 125 °C	I _D	91		
Continuous Source Current (Diode Conduction) ^a		I _S	120	А	
Pulsed Drain Current ^b		I _{DM}	300		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	80		
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	320	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	Р	250	W	
	T _C = 125 °C	P _D	83	۷V	
Operating Junction and Storage Temperature Rar	nge	T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-Ambient	PCB Mount ^c	R _{thJA}	40	°C/W		
Junction-to-Case (Drain)		R _{thJC}	0.6	C/W		

Notes

a. Package limited.

b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

c. When mounted on 1" square PCB (FR4 material).

d. Parametric verification ongoing.

1

SQV120N06-4m7L



Vishay Siliconix

SPECIFICATIONS ($T_C = 25 \degree C$, unless othe	rwise noted)			1	T		
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static								
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0, I_D = 250 \ \mu A$		60	-	-	v	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$		2.0	2.5	v	
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS}=0~V,~V_{GS}=\pm~20~V$		-	± 100	nA	
		$V_{GS} = 0 V$	V _{DS} = 60 V	-	-	1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 60 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	500		
On-State Drain Current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	120	-	-	Α	
		$V_{GS} = 10 V$	I _D = 30 A	-	0.00378	0.00470	Ω	
Drain-Source On-State Resistance ^a	D	$V_{GS} = 10 V$	$I_D = 30 \text{ A}, T_J = 125 \ ^\circ\text{C}$	-	-	0.00801		
Drain-Source On-State Resistance ~	R _{DS(on)}	$V_{GS} = 10 \text{ V}$	$I_D = 30 \text{ A}, T_J = 175 \ ^\circ\text{C}$	-	-	0.00992		
		$V_{GS} = 4.5 V$	I _D = 20 A	-	0.00481	0.00600		
Forward Transconductance b	g _{fs}	V _{DS}	= 15 V, I _D = 30 A	-	118	-	S	
Dynamic ^b				<u> </u>	1		<u>.</u>	
Input Capacitance	C _{iss}			-	6705	8800		
Output Capacitance	C _{oss}	$V_{GS} = 0 \ V \qquad \qquad V_{DS} = 25 \ V, \ f = 1 \ MHz$	-	904	1200	pF		
Reverse Transfer Capacitance	C _{rss}				555		800	
Total Gate Charge ^c	Qg			-	148	230		
Gate-Source Charge ^c	Q _{gs}	$V_{GS} = 10 \text{ V}$	$V_{DS} = 30 \text{ V}, \text{ I}_{D} = 85 \text{ A}$	-	21.4	-	nC	
Gate-Drain Charge ^c	Q _{gd}			-	33.2	-		
Gate Resistance	Rg	f = 1 MHz		0.45	0.99	1.5	Ω	
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD}=30~V,~R_L=0.353~\Omega$ $I_D\cong85~A,~V_{GEN}=10~V,~R_g=1~\Omega$		-	16	25		
Rise Time ^c	tr			-	9	15	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	46	75		
Fall Time ^c	t _f			-	12	20		
Source-Drain Diode Ratings and Characteristics ^b								
Pulsed Current ^a	I _{SM}			-	-	300	А	
Forward Voltage	V _{SD}	$I_{\rm F} = 70 \text{ A}, V_{\rm GS} = 0$		-	0.92	1.5	V	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

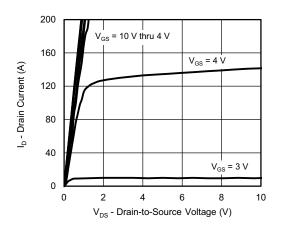
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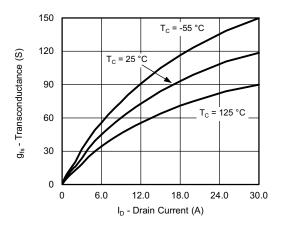
SQV120N06-4m7L

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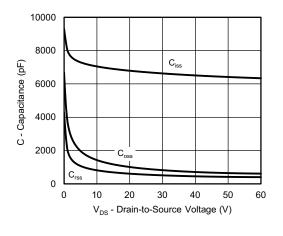
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



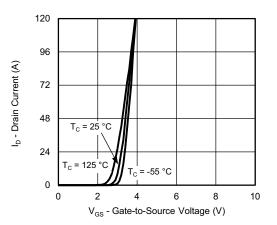
Output Characteristics



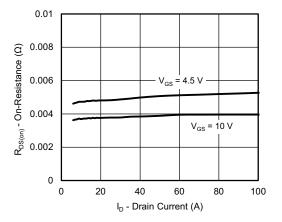
Transconductance



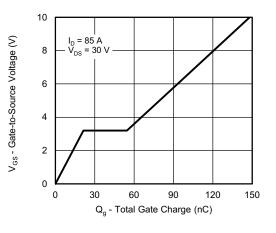
Capacitance



Transfer Characteristics



On-Resistance vs. Drain Current



Gate Charge

S15-2326-Rev. A, 05-Oct-15

3

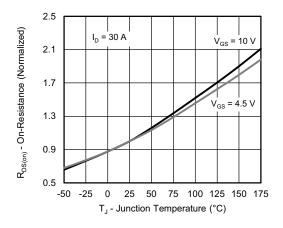
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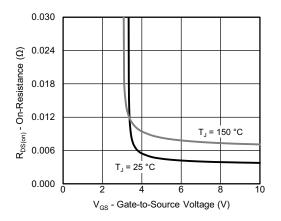




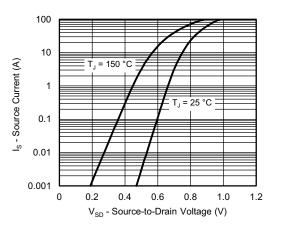
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



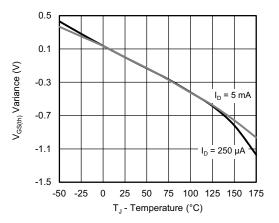
On-Resistance vs. Junction Temperature

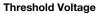


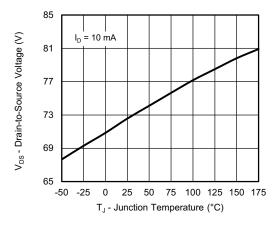
On-Resistance vs. Gate-to-Source Voltage



Source Drain Diode Forward Voltage







Drain Source Breakdown vs. Junction Temperature

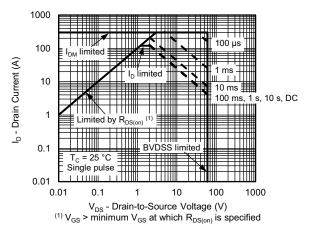
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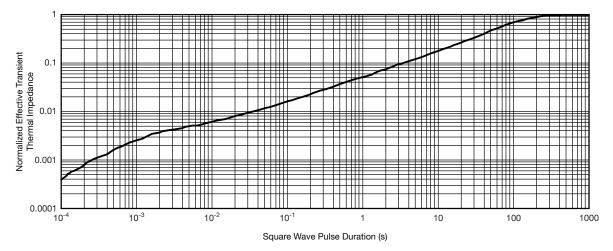




THERMAL RATINGS ($T_A = 25 \text{ °C}$, unless otherwise noted)



Safe Operating Area

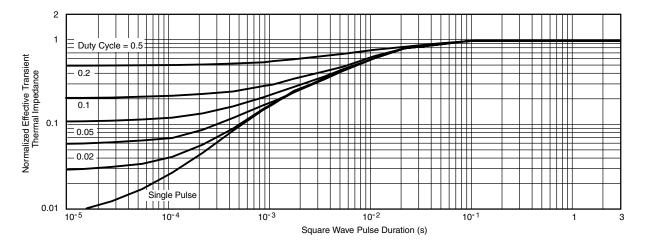


Normalized Thermal Transient Impedance, Junction-to-Ambient



Document Number: 66962

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

The characteristics shown in the two graphs

S15-2326-Rev. A, 05-Oct-15

- Normalized Transient Thermal Impedance Junction to Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction to Case (25 °C)

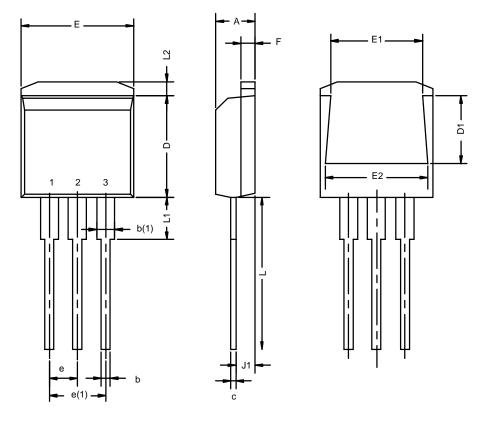
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <u>www.vishay.com/ppg?66962</u>.



Package Information Vishay Siliconix

TO-262: 3-LEAD



	MILLIM	ETERS*	INC	HES	
Dim	Min	Max	Min	Max	
Α	4.32	4.70	0.170	0.185	
b	0.64	1.00	0.025	0.039	
b(1)	1.14	1.40	0.045	0.055	
С	0.36	0.50	0.014	0.020	
D	8.64	9.65	0.340	0.380	
D1	5.59	6.10	0.220	0.240	
е	2.41	2.67	0.095	0.105	
e(1)	4.95	5.33	0.195	0.210	
E	10.03	10.41	0.395	0.410	
E1	7.87	8.64	0.310	0.340	
E2	9.02	9.53	0.355	0.375	
F	1.14	1.40	0.045	0.055	
J1	2.41	2.79	0.095	0.110	
L	13.08	14.22	0.515	0.560	
L1	-	3.81	-	0.150	
L2	1.02	1.40	0.040	0.055	
ECN: T-02234—Rev. C, 14-Oct-02 DWG: 5855					

*Use millimeters as the primary measurement



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